

OTS: 60-11,400

JPRS: 2380

22 March 1960

ELECTROCHEMICAL STORAGE ELEMENT

- USSR -

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19980109 170

JPRS: 2380

CSO : 3107-N

ELECTROCHEMICAL STORAGE ELEMENT

This is a translation of an article written by A. A. Nazarov, Yu. V. Petrov and A. A. Zhdanov in Izvestiya Vysshikh Uchebnykh Zavedeniy -- Priborostroyeniye (News of the Higher Educational Institutions -- Instrument Building) Vol No 6, 1958, pages 50-53/

The development of computing technology gives rise to demands for the creation of various types of storage devices, capable of receiving information from the arithmetic units of the computer machine, storing it, and issuing it whenever required.

For various types of computer machines various types of memory devices are necessary which differ in their properties.

In some cases there come to the forefront requirements of high speed, fast recording rate and fast reading rate, while in other cases, for example in relay machines, or else in certain special-purpose machines, no great speed is required, but on the other hand the paramount requirements become small size of the memory element, low power consumption, simplicity, and low cost in manufacture.

There exist a large number of various types of memory elements, based on electric and magnetic principles.

In the present article we describe a memory element constructed on the chemical principle.

The principal requirements that must be satisfied by chemical memory elements of modern computing machines are high speed of the chemical processes and their reversibility, i.e., the possibility of multiple recording of the information. Many chemical processes satisfy the requirement of reversibility (phase changes connected with the formation of new modifications, many reversible chemical reactions, etc.). However, these processes, particularly those occurring in the solid phases, are very slow -- on the order of tens of minutes and more -- which excludes them from use in computing machines.

The requirement of high speed is satisfied by reactions that occur explosively. Explosive reactions, however, are as a rule irreversible, and to return the memory element to its initial stage it is necessary to add a rather complicated construction, even if one disregards the fact that the reverse process is many times slower than the direct one.

Memory elements free of these shortcomings are based on electrochemical processes of deposition and dissolution of metals on electrodes immersed in an electrolyte solution through which an electric current flows.

In our case the speed of the process is determined by the speed of deposition of the metal on the electrodes. Under known conditions the process is fully reversible.

As is known, when a metal is immersed in a solution of salt with cations of the same kind, at a definite concentration of this salt, the metal has a fully defined electrode potential

$$E = E_0 + k \ln a,$$

where E -- electrode potential of the metal,
E₀ -- the standard electrode potential,
a -- the activity of the cations in the solution,
k -- a constant (when T = const).

If another metal is deposited on this metal, and if the other metal has a more negative electrode potential, then the common electrode potential of the system as a whole will be closer to the potential of the second metal. If the deposited metal has a very small concentration, its potential cannot be measured, and can be determined only starting with a certain finite concentration. The time during which the precipitated metal accumulates on the electrode will indeed be the time of operation of the given memory element. It can be calculated by the Faraday formula.

Thus, there is a real possibility of using electrochemical processes of deposition of a metal on an electrode for recording information whenever a current pulse passes through the cell, or the return of the metal in the form of an ion into the solution whenever a current pulse of opposite polarity passes through the cell to erase the information.

Let us consider the construction of the proposed memory element. This element is an electrochemical cell, consisting of three electrodes: one zinc and two of the same metal -- working and standard, which are plates of refined copper amalgamated with mercury. The passage of a current pulse causes zinc to be deposited on the working electrode and to change the potential of this electrode, while the standard electrode has a fixed stable potential. The working and the zinc electrodes are in one vessel, the standard electrode is in another one, and both vessels are connected by means of an electrolytic key (Fig. 1). The electrolyte used is a saturated solution of zinc sulphate with a small amount of mercurous sulphate added.

To record the information we apply a plus voltage to the zinc electrode and a minus voltage to the working electrode. Zinc is deposited on the working electrode in accordance with the following reaction



A zinc amalgam is produced, and the following electromotive force is produced between the working and standard electrodes:

$$\Delta\varphi = \varphi_{\text{Cr}} - \varphi_{\text{Zn}},$$

The magnitude of the electromotive force for electrodes made of amalgam of copper and zinc is 1.1 volt.

Figure 2 shows the variation of the emf with time during the process of recording and erasure. These data show that the current delay of the element coincides with the time delay of ordinary electromagnetic relays, which makes it possible to use this electrochemical memory element extensively in relay computing machines.

No separate voltage source (1.5 volts) is needed for the recording of the information, as the 12 volt standard used in relay circuits can be used, since in character of operation of the cell.

We considered above the operating principle and the operation of an individual memory cell. If cells are joined in a common block, the zinc and standard electrodes of the latter are interconnected and consequently, one zinc and one standard electrode is used in a system containing several working electrodes.

Generally speaking, zinc is deposited on the standard electrode during recording, but since the area of the standard electrode is chosen such that it exceeds by many times the areas of the working electrodes, the processes that occur on the standard electrode during the recording time (accumulation of zinc amalgam) can be neglected. During erasure the zinc on the standard electrode is dissolved. The authors have prepared an experimental block consisting of 48 elements, measuring 70 x 30 x 20, i.e., each element occupies approximately 1 cubic centimeter. Such a structure readily admits of mechanization of the manufacture by stamping. One first stamps the upper part of the vessel together with the working and combined zinc and standard electrodes, and then, after forming the amalgam on the electrodes (the electrodes are held in a solution of mercury nitrate for 10 or 15 minutes) the bottom is glued to the vessel. The vessel is filled with the electrolyte through two holes in the upper portion, which are then tightly closed by threaded plugs. In such a method a large number of elements is prepared immediately, the cost of manufacture per element will obviously be small.

Let us examine now the question of using this element in the general circuitry of a computer machine.

In order that no information be lost during the process of recording, the electrode current must not be greater than 10--15 microamperes. For this purpose the recording can be made through a high-resistance amplifier, the output power of which is in turn sufficient for operation of an electromagnetic relay.

The authors have used an amplifier made up of two PLE diodes; the input resistance was 100,000 ohms, the amplifier produced practically unlimited number of reading cycles. Since the amplifier is larger and more expensive than the memory cell itself, the address decoder should ensure operation of a large number of memory elements per amplifier. One of the possible solutions is to use a stepping selector as a decoder. Thus, a stepping selector ShI-50/8 can operate with 400 memory cells (50 eight-digit binary numbers) using eight amplifiers (one amplifier for each column in all 50 numbers).

Conclusion

Electrochemical memory elements can be used successfully in relay computing machines and special machines which do not require high working speeds.

Received 18 September 1958

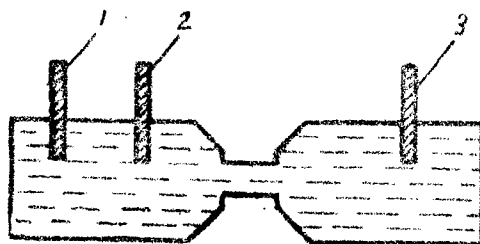


Figure 1. Section through the memory element.

- 1 -- zinc electrode, 2 -- working electrode,
- 3 -- standard electrode

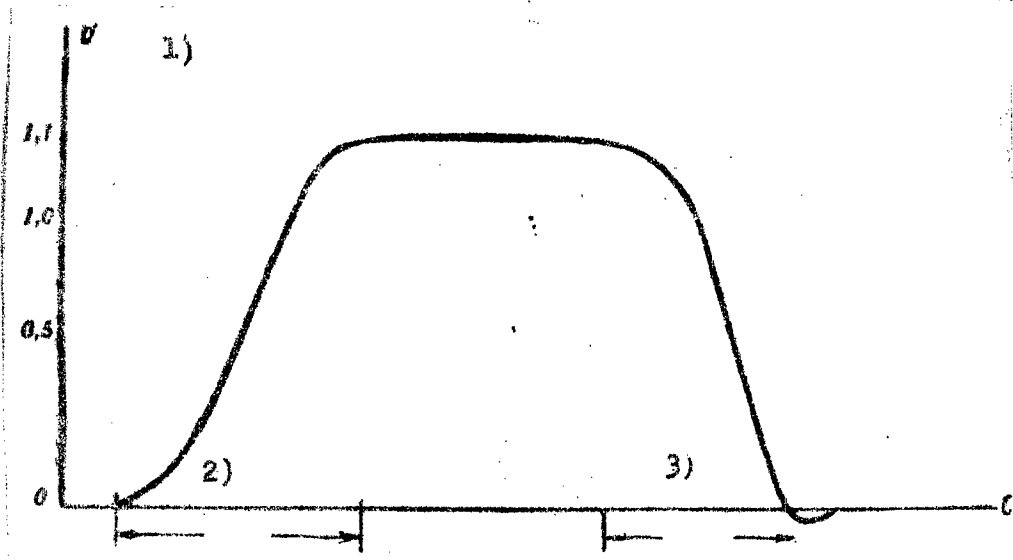


Figure 2. Recording and erasure processes

- 1) U, volts
- 2) Recording, 30 milliseconds
- 3) Erasure, 20 milliseconds

END